

VERTEX2005 Conferenceの報告

KEK-IPNS
関本 美知子

VERTEX Conference とは・・・

- 第1回目のConferenceは、FinlandのBasto Islandで1992年に開かれた。この時はCERNのDELPHIなど約3つのプロジェクトに関して、誰でも (physicists, engineers, hardware, software...) 参加し、フリップを使用して (no power!) 議論された。
- 以後、世界の「water front」を会議の場として選びながら、毎年開催されてきた。

(Slovenia, USA, Israel, Italy, Brazil, Greece, Netherlands, USA, Switzerland, Hawaii, UK, Italy)

- VERTEX2005は第14回にあたり、
Asiaでは初めて日本の日光中善寺湖畔で開催された。

Basto

vs

Nikko



Vertex 1992

A few detailed talks – physics, electronics..
Many questions and discussions
No summary or proceedings

Sauna & cold sea

Vertex 2005

Many talks – review + details
Some questions & discussions
Summary

Bath & cold wind

from Tyndel's summary

The VERTEX Series is International Workshop on Vertex Detectors

Emphasis is usually given to topics directly related to vertex detectors:

- Vertex detectors at present experiments
- New vertex detector projects
- R&D for future vertex detectors
- Radiation hardness of detectors and R&D on new materials
- Radiation hardness of integrated readout electronics
- DAQ and trigger architecture for vertex detectors
- Vertexing algorithms and performances
- Applications of vertexing instrumentation to other fields.

Additional talks usually available for new and innovative ideas and applications.

VERTEX2005@ *Lakeside Hotel, Chuzenji Lake, Nikko*

Local Organizing Committee: Chair; A. Miyamoto (KEK),
J. Haba (KEK), Y. Unno (KEK),
Y. Sugimoto (KEK)

- 参加者: 外国から35人、日本から15人
- 日程: 2005.11.7 9:00 ~ 11.11 12:00

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2006.01.26-27

RCNP Workshop on MPGD and
Pixel Detectors

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- 日程 & 報告数: 2005.11.7 9:00 ~ 11.11 12:00
40件 (各30分or20分)
- 報告された研究所 & グループ、他分野:

KEK; *BELLE, K2K(T2K)*

CERN; *ATLAS, CMS, LHCb, ALICE, DESY; ZEUS*

FNAL; *D0, CDF, SLAC; BaBar* BNL; *PHENIX*

future projects; *ILC, S-LHC, S-Bfactory*

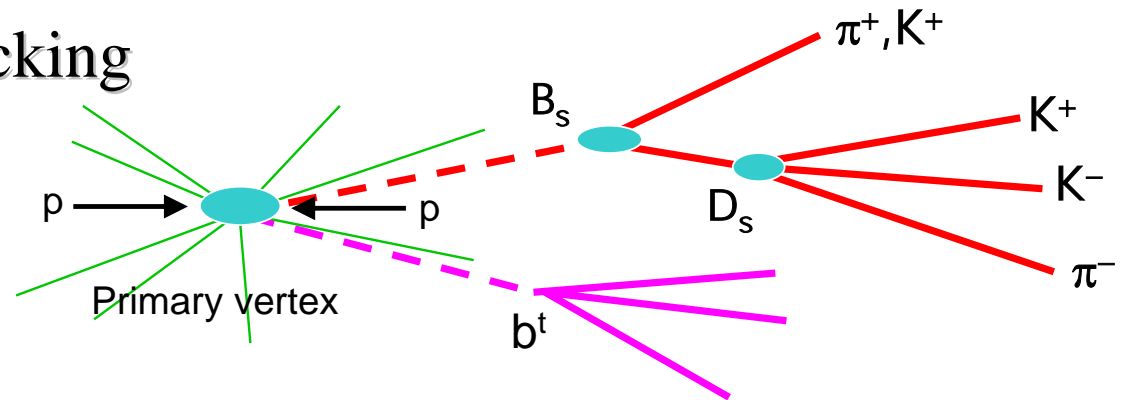
other fields; 医学、核融合、宇宙、放射光

何が報告されたか？

- 7 operating experiments
 - each with 1-3 Si technologies
 - Most with upgrade plans
- 11 projects under construction
- 20 RD efforts or specialised techniques
- 4 from other fields

from Tyndel's summary

Vertexing & tracking



1. Measure the first point precisely (1 or 2D) & with 'no' material
 - Material perturbs trajectories (mrad) $\sim 1.4 \cdot \sqrt{tX0(\%)/p(\text{GeV})}$
2. Measure the angle precisely
 - Goal is that the multiple scattering in the beam pipe/first layer should dominate i.e. $s \sim 1\text{mrad}$
3. Measure the curvature
 - Precision $\sim L2$. Value is driven by physics (charge ID; mass resolution)
4. ...and cover a large solid angle

• In principle simple but in detail complicated (as we have heard) !

Silicon system performance

- *I had thought to gather and compare performance figures. Impossible & probably of no use. Much more fun (for me and you) to collate problems and ideas & try and learn lessons.*

Typical values today

- Resolution - rf z
- Granularity or cell size

Missing short strips/macro-pixels →

- FE Speed & noise
- Power/channel (1msec – 25nsec)
- Material in X0
- Geometry and sImpact
- Efficiency

< 10mm

20x20mm² (CCD, APS, DF)

0.02 mm² (pixels)

10.0 mm² (strips)

25nsec, S/N ~ 20

1 ~ 5mW (strips LC-LHC)

0.1mW(pixels);

0.1mW(CCDs)

1%(strips); 2%(pixels)

< 20mm from beam; ~20mm

b-tags and some c-tag?

99%(build) – 85%(running)

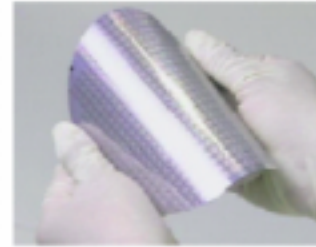
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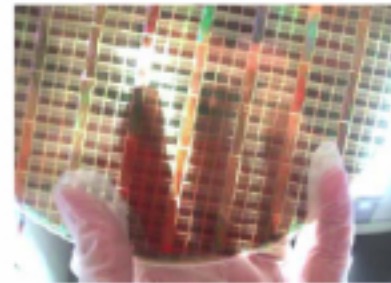
- 詳しくは、<http://www-conf.kek.jp/vertex2005>のプログラムを参照してください。
- 特に、M. Tyndel (RAL)の*Summary*によくまとめられています。
- また、R. Yarema (Fermilab)がElectronicsの立場からHEPの将来計画にむけてまとめられています。

Wafer Thinning

- Detectors and readout chips make a significant contribution to multiple scattering
 - Every 100 μ of silicon is 0.1% X_0
 - Hybrid pixels have 2 layers of silicon, each greater than 100 μ thick
- Take advantage of work being done in industry by major companies (IBM, INTEL, Toshiba, etc.) to reduce wafer thickness
- Thinning
 - Thinning to 50 microns is in production
 - State of the art – CMOS wafers thinned to 10-15 microns by lapping/grinding followed by wet or plasma etch and CMP. Thinner for SOL.
- Challenges
 - *Handling/breakage*
 - *Thickness uniformity on large wafers*
 - *Circuit performance changes due to thinning*
 - *No change in V_t for 25u wafer (Fraunhofer, IZM)*
 - *No change in I_{dsat} for 25 u wafers (IZM)*
 - *More tests needed*



Thinned IC wafer (J. Joly, LETI)



Thinned 200 mm wafer transferred on to glass handle wafer (A. Young, IBM)

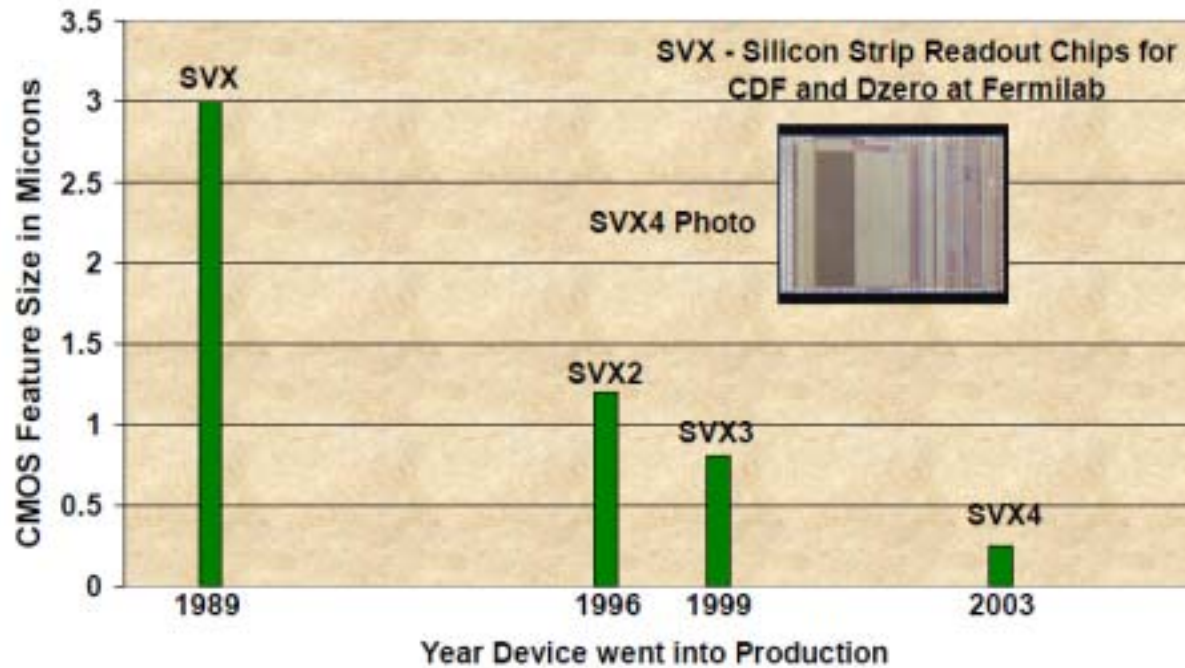
November 7-11, 2005

Vertex 2005, Nikko, Japan

11

CMOS Feature Size Decrease

SVX Feature Size vs. Year

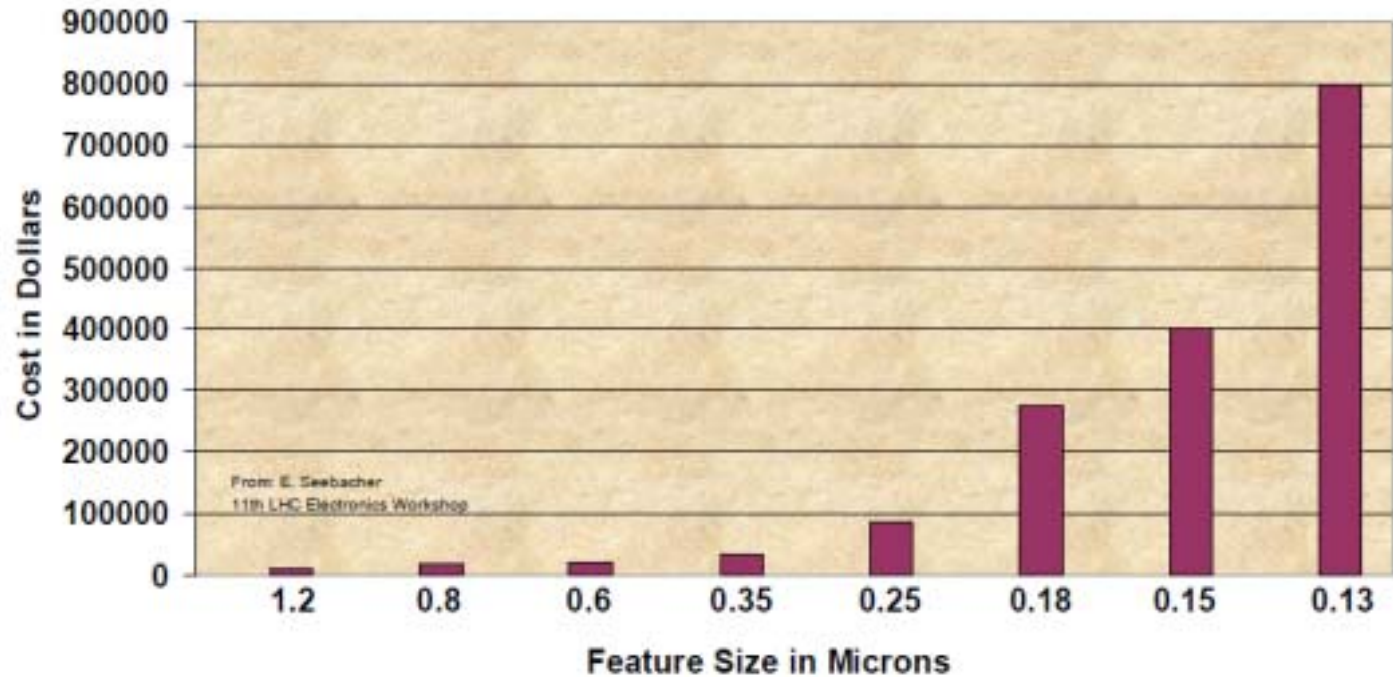


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25

Mask Cost for CMOS Processes



November 7-11, 2005

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28

Challenges and the Future

- Technology tradeoffs must be made depending on the application.
- As a general rule good tools and experienced designers will reduce the number of design iterations saving development time and overall cost.
- A few questions to think about
 - What is the proper balance between on chip regulation (higher power dissipation) with the potential reduction in cabling mass and power?
 - Will special design rules still be necessary at smaller CMOS features sizes, or at what level will the special design rules be necessary
 - Will wafer thinning and 3D circuits become practical for HEP
 - Can power ramping be made to work in future very large systems
 - Readout stability
 - Thermal cycling
 - Pickup
 - Can analog information be given up to reduce system complexity and reduce power dissipation?
 - Can designs be tested in larger feature sizes to save development money
 - Similar thing was done before with rad soft to rad hard design process.
- Many questions – lots of work to be done
- Start thinking now - the future is just around the corner



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29

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- また、R. Yarema (Fermilab)がElectronicsの立場からHEPの将来計画にむけてまとめられています。
- 「高エネルギーニュース」最新号(今月配布?)に、講演者とその簡単なトピックをまとめたものが報告されています。個々の講演を検索する参考にしてください。

検出器製作において参考になる

(関本が捉えた) keywords

- I. Radiation-hardness
- II. Humidity
- III. Kapton Technology

I. Radiation-hardness

- Review all components for radiation hardness
 - Include all ASICs, opto-links, glues
- Build in radiation & beam loss monitors
 - There is a lot of energy in beams
 - Can cause physical damage
 - Results in damage to
 - Silicon (pinholes in Belle)
 - ASICs (many expts)
 - Power supplies (CDF)...
 - **Diamonds** are now available as BCMs

I. Radiation-hardness

- Belle: Luminosity ($1.6 \times 10^{34} \text{cm}^{-1} \cdot \text{s}^{-2}$) $\times 3$ @ 2007
トリガー系のupdate

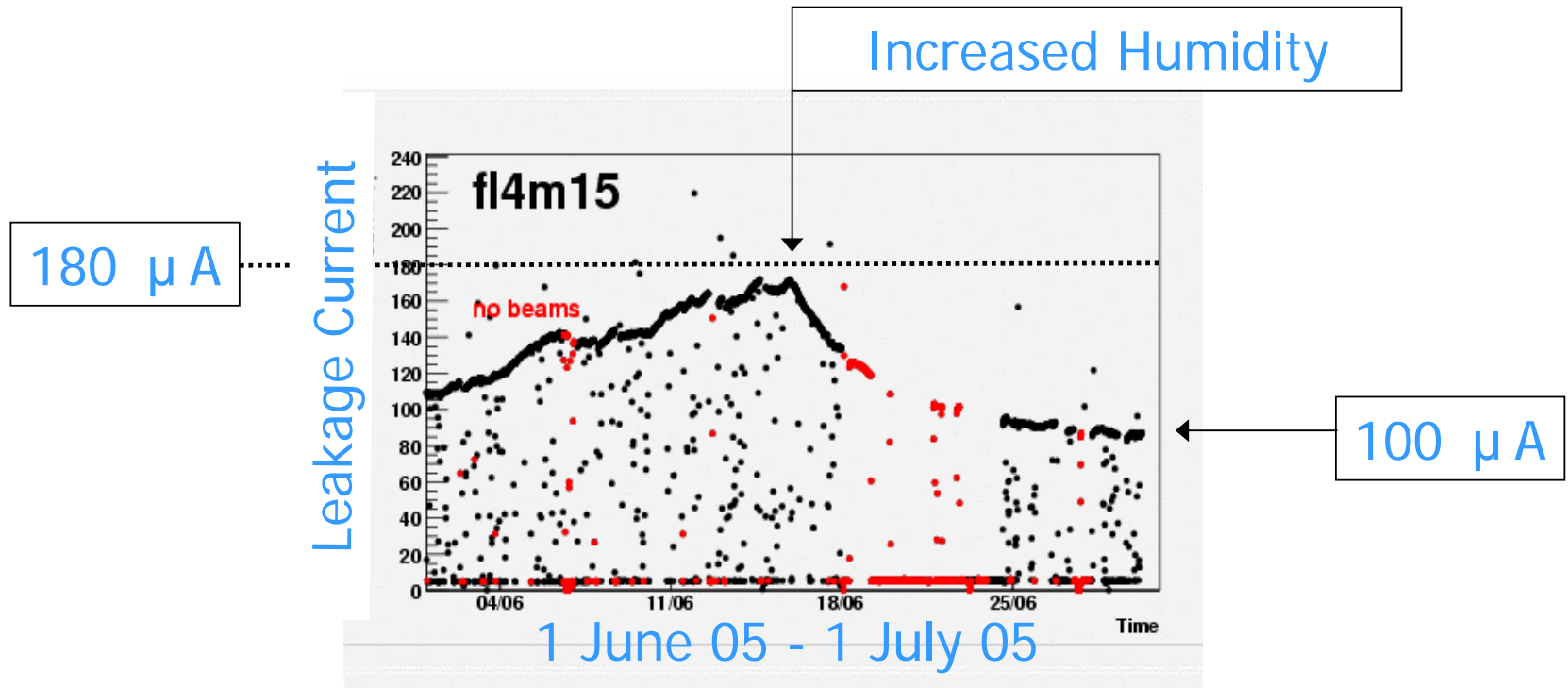
 $\times 30$ @ Super-B monolithic active pixel sensor
continuous acquisition pixel (CAP)
- ATLAS: 集積 Luminosity $\sim 3000 \text{fb}^{-1}$ @ SLHC
diamond pixel detector
- Czochralski silicon: 耐放射線の強いシリコン(結晶の成長方法による違い)
- and of course, future big projects, not only HEP but also NP and others
needs the new technologies for radiation-hardness

II. Humidity

- Surface charge: depend on humidity, temp
Micron detectors in BarBar
- Leakage current: more humidity helps to stop the effect
“Humidity plays a role”

Leakage Current Increase

Using humid air and a new reference voltage setting, the situation now is under control



II. Humidity

- Surface charge: depend on humidity, temp
Micron detectors in BarBar
- Leakage current: more humidity helps to stop the effect
“Humidity plays a role”
- Corrosion:
CMS discovery that Humidity reacts with Phosphorus (present in a 4% concentration into the passivation oxide) and forms an acid that corrodes Aluminum.

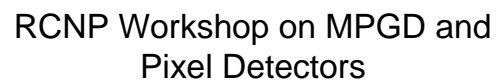
Corrosion on Silicon Sensors

A „How to Eat up Your Detector at the Very End!“

Günther Beuchle, Jean-Charles Fontaine, Martin Frey,
Alexander Furgeri, Frank Hartmann, Manfred Krammer



A photograph of a heavily rusted, dark-colored vintage car, likely a Volkswagen Beetle, with significant damage to the front end and body. The car is parked outdoors on a dirt surface, and its interior, including the steering wheel, is visible through the open windows.



The mystery solved, ...

- Stains & dots need **voltage**, **time**, **humidity**
- Yes, we all test under bias voltage!
 - The company tests only 4 min! → no stains & dots
 - Karlsruhe & Vienna test with low humidity
 - Strasbourg long term tests sensors from everywhere

BUT, what is it?

And is it dangerous?

この話題に関して興味のある方は、



<http://www-conf.kek.jp/vertex2005>

Wednesday 09 November 2005

Short Talks and FE Electronics

(09:00->11:50)

Chair: David Christian
(FNAL)



Room: Lakeside Hotel--Kaede

Corrosion of Silicon Sensors (20')

Frank Hartmann
(IEKP Karlsruhe, CERN)

を参照してください。



III. Kapton Technology

- ATLAS, CMS, GLAST all had problems with Kapton
- High density (70mm) Al pitch adaptors for PHENIX
- Fine pitch (100mm) tab-bonding on ALICE SSD
- and

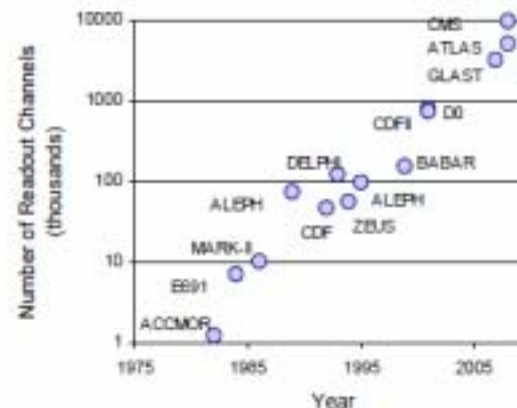
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自分の仕事と関係ない・・・と思っているところに、
今直面している問題解決や、新しい種がたくさん
あることを改めて実感したexcitingな5日間でした。

Worm (RAL) によれば、

What is the next "Big Thing" for vertexing?

- The tracking challenges of reconstructing b/c in high-speed, modern detectors have been met by silicon.
 - Is there room for improvement?
 - What is the next challenge?
- Bigger?
 - Industrialization of silicon modules made CMS, ATLAS possible
 - More standardisation and simplification needed for any next step
- Better!
 - New technologies(?)
 - Better/thinner detector means charge identification possible
 - Excellent precision in $r\phi$ and z ; can reconstruct neutrinos in semileptonics

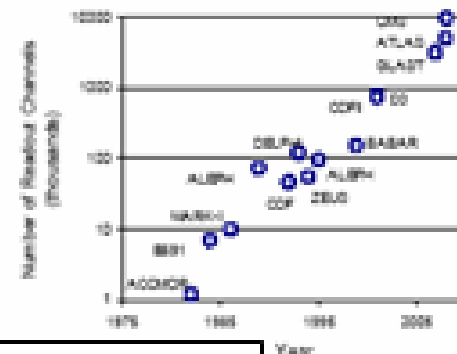


Better detectors needed:

Lower mass, better precision → better understanding of the physics

Silicon system evolution – Physicist Moores Laws

- Moores law is often quoted in microelectronics to indicate an exponential change. Compare the situation in 1992 and 2005. Typical values (not the extremes).*



	< 1992	2005	Factor	Doubling time
ASIC feature size	5 $\mu\text{m} \times 5 \mu\text{m}$	0.25 $\mu\text{m} \times 0.25 \mu\text{m}$	400	1.5y
Sensor area	0.5 m ²	100 m ²	200	1.7y
Sensor cost/cm ²			0.1	4y
Strip channels	10 ⁵	10 ⁷	100	2y
CCD channels	$\sim 10^3$	10 ³ - 10 ⁴		-
FE speed	μsec	10 nsec	100	2y
Power/ch	mW	mW	1	compensation

- Cannot extrapolate – hit physical (& financial limits)**

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Worm (RAL) によれば、
今や “biggerよりもbetter detectors” が必要である！

ということは、量より質・・・ならば我々にもチャンスがある！？・・・may be

三人寄れば文殊の知恵！互いのcommunicationを密にして
MPGD研究会等を盛り上げていって独創性を高めていき、

VERTEX2006 には・・・

是非、日本からも報告を沢山出しましょう！